

10/023113

12/13/01

PATENT NUMBER and
ISSUE DATE

U.S. UTILITY Patent Application

APPL NUM 10023113	FILING DATE 12/13/2001	CLASS 265	SUBCLASS	GAU 2818	EXAMINER
**APPLICANTS: Marshall Andrew Kim Youngmin Scott David Mercer Douglas					
**CONTINUING DATA VERIFIED: THIS APPLN CLAIMS BENEFIT OF 60/159324 01/03/2001					
<h1>BEST AVAILABLE COPY</h1>					
** FOREIGN APPLICATIONS VERIFIED:					
PG-PUB <input type="checkbox"/> DO NOT PUBLISH <input type="checkbox"/>		RESCIND <input type="checkbox"/>			
Foreign priority claimed <input type="checkbox"/> yes <input type="checkbox"/> no 35 USC 119 conditions met <input type="checkbox"/> yes <input type="checkbox"/> no Verified and Acknowledged Examiners' initials				ATTORNEY DOCKET NO TI-31157	
TITLE : Memory cell with transistors having relatively high threshold voltages in response to selective gate doping					

NOTICE OF ALLOWANCE MAILED		CLAIMS ALLOWED	
		Total Claims	Print Claim for O.G.
ISSUE FEE		DRAWING	
Amount Due	Date Paid	Sheets Drwg.	Figs. Drwg. Print Fig.
<input type="checkbox"/> TERMINAL DISCLAIMER		Primary Examiner	
		Application Examiner	
PREPARED FOR ISSUE		WARNING: The information disclosed herein may be restricted. Unauthorized disclosure may be prohibited by the United States Code Title 35, Sections 122, 181 and 368, Possession outside the U.S. Patent & Trademark Office is restricted to authorized employees and contractors only.	

FILED WITH:

☐ DISK (CRF)

☐ CD-ROM

(Attached in pocket on right inside flap)